

App. No. 10/805,992
Office Action Dated March 25, 2005

Amendments to the Claims:

This listing of claims will replace all prior versions and listing of claims in the application.

Claims 9 and 16 are amended.

Claim 15 is canceled.

Listing of Claims:

1-8. (Canceled)

9. (Currently Amended) A method for producing a semiconductor device, comprising:
forming a semiconductor member including a SiC member and a SiGe member on a SiC substrate by crystal growth; and forming an ohmic electrode on the semiconductor member, and forming a gate electrode on the SiC member.

10. (Original) A method for producing a semiconductor device according to claim 9, wherein the process of forming the semiconductor member by crystal growth includes forming a SiGe member on SiC member by crystal growth.

11. (Original) A method for producing a semiconductor device according to claim 9, wherein the process of forming the semiconductor member by crystal growth includes forming a Si member on a SiC member by crystal growth; and forming a SiGe member on the Si member by crystal growth.

12. (Original) A method for producing a semiconductor device according to claim 9, wherein the process of forming the semiconductor member by crystal growth includes forming a semiconductor member, in which a mole fraction is varied continuously from SiC to Si and from Si to SiGe, on a SiC member by crystal growth.

App. No. 10/805,992
Office Action Dated March 25, 2005

13. (Original) A method for producing a semiconductor device according to claim 9, wherein the process of forming the semiconductor member by crystal growth includes forming a semiconductor member, in which a C mole fraction is decreased while a Ge mole fraction is increased continuously from SiC to SiGe, on a SiC member by crystal growth.

14. (Original) A method for producing a semiconductor device according to claim 9, wherein the semiconductor member is formed on both a p-type region and an n-type region by crystal growth

15. (Canceled)

16. (Currently Amended) A method for producing a semiconductor device according to claim [[15]]9, wherein the gate electrode is formed on a Si oxide film.